

Rafik M Imamov

List of Publications by Year in descending order

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Version: 2024-02-01

13
papers

110
citations

1684188

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1372567

10
g-index

13
all docs

13
docs citations

13
times ranked

71
citing authors

#	ARTICLE	IF	CITATIONS
1	Asymmetric X-Ray Diffraction. Crystallography Reviews, 1992, 3, 157-226.	1.5	42
2	Metamorphic InAlAs/InGaAs/InAlAs/GaAs HEMT heterostructures containing strained superlattices and inverse steps in the metamorphic buffer. Journal of Crystal Growth, 2013, 366, 55-60.	1.5	23
3	Structural and electrical properties of quantum wells with nanoscale InAs inserts in $\text{In}_{1-y}\text{Al}_y\text{As}/\text{In}_{1-x}\text{Ga}_x\text{As}$ heterostructures on InP substrates. Crystallography Reports, 2011, 56, 298-309.	0.6	11
4	Study of new designs for the InAlAs metamorphic buffer on GaAs substrates with distributed compensation of elastic deformations. Semiconductors, 2013, 47, 997-1002.	0.5	8
5	X-Ray diffractometry of metamorphic nanoheterostructures. Crystallography Reports, 2014, 59, 258-265.	0.6	8
6	<title>Structural diagnostics of quantum layers by x-ray diffraction and standing waves</title>. , 2004, 5401, 543.		5
7	Study of the influence of strained superlattices introduced into a metamorphic buffer on the electrophysical properties and the atomic structure of InAlAs/InGaAs MHEMT heterostructures. Semiconductors, 2013, 47, 532-537.	0.5	4
8	Structural and electrical properties of InAlAs/InGaAs/InAlAs HEMT heterostructures on InP substrates with InAs inserts in quantum well. Crystallography Reports, 2014, 59, 900-907.	0.6	3
9	Structural characterization of interfaces in the $\text{Al}_x\text{Ga}_{1-x}\text{As}/\text{GaAs}/\text{Al}_x\text{Ga}_{1-x}\text{As}$ heterostructures by high-resolution X-ray reflectometry and diffractometry. Crystallography Reports, 2005, 50, 739-750.	0.6	2
10	Electrical and structural characteristics of metamorphic $\text{In}_{0.38}\text{Al}_{0.62}\text{As}/\text{In}_{0.37}\text{Ga}_{0.63}\text{As}/\text{In}_{0.38}\text{Al}_{0.62}\text{As}$ HEMT nanoheterostructures. Crystallography Reports, 2013, 58, 914-919.	0.6	2
11	Electrophysical characteristics and structural parameters of metamorphic HEMT nanoheterostructures $\text{In}_{0.7}\text{Al}_{0.3}\text{As}/\text{In}_{0.7}\text{Ga}_{0.3}\text{As}/\text{In}_{0.7}\text{Al}_{0.3}\text{As}$ containing superlattices with different numbers of periods in the metamorphic buffer. Crystallography Reports, 2014, 59, 425-429.	0.6	2
12	Study of the relationship between the crystal structure of nanolayers and electrical properties in $\text{Al}_x\text{Ga}_{1-x}\text{As}/\text{In}_y\text{Ga}_{1-y}\text{As}$ pseudobinary heterostructures by double-crystal X-ray diffraction. Crystallography Reports, 2008, 53, 183-186.	0.6	0
13	The electrical and structural properties of $\text{In}_y\text{Ga}_{1-y}\text{As}/\text{In}_x\text{Al}_{1-x}\text{As}/\text{InP}$ quantum wells with different InAs content. Crystallography Reports, 2010, 55, 6-9.	0.6	0